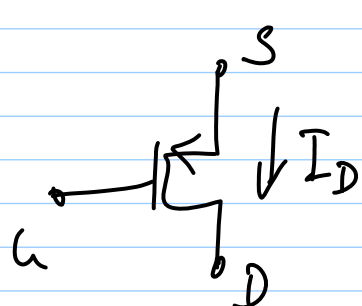
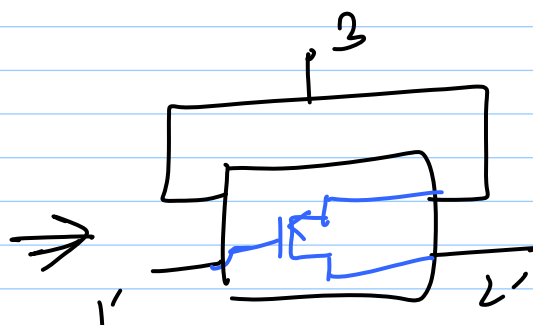
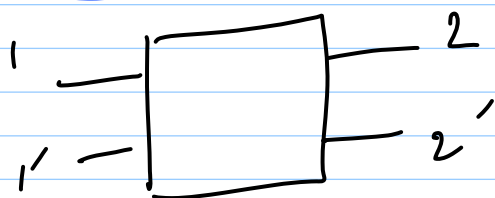


10-10-12

Lec 29

PMOS transistor



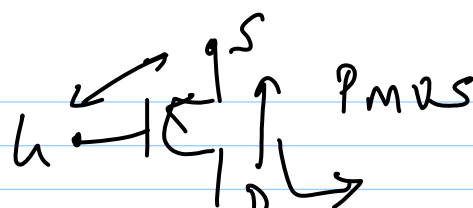
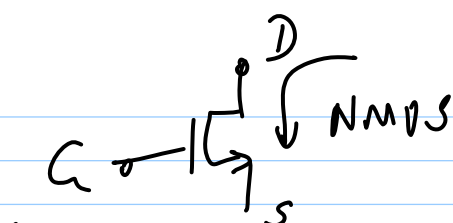
Sat.

$$I_D = \frac{1}{2} \mu_p \epsilon_{ox} \frac{W}{L} (V_{SG} - V_{TP})^2 (1 + \lambda_p V_{SD})$$

non-sat. (triode)

$$I_D = \mu_p \epsilon_{ox} \frac{W}{L} \left\{ (V_{SG} - V_{TP}) V_{SD} - \frac{V_{SD}^2}{2} \right\}$$

o.p. x



* I_D flows into

①

* For sat.

$$V_D \gg V_S$$

$\Rightarrow V_D$ can go on V_T below V_G

* $V_{GS} \geq V_{TN}$ for $I_D > 0$

* $V_{TN} > 0$ for enhancement mode device

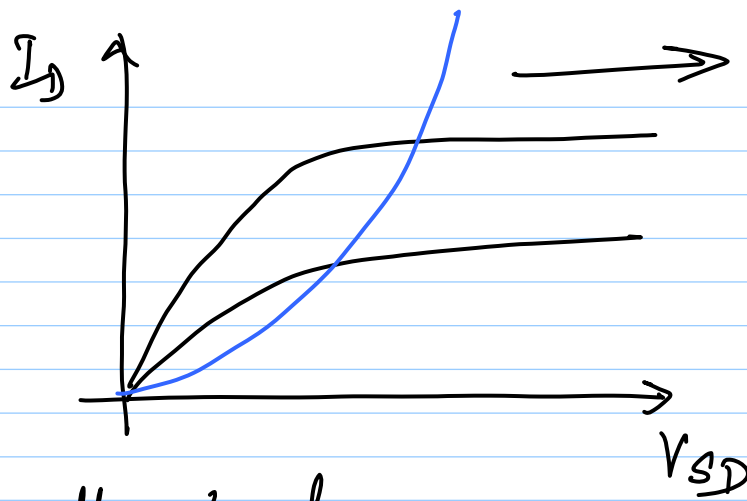
* I_D flows out of ②

* For sat. $V_D < V_S$

$\Rightarrow V_D$ can go V_T above V_G ($V_D \leq V_G + V_T$)

* $V_{SG} \geq V_{TP}$ for $I_D > 0$

* $V_{TP} > 0$ for enh. mode PMOS

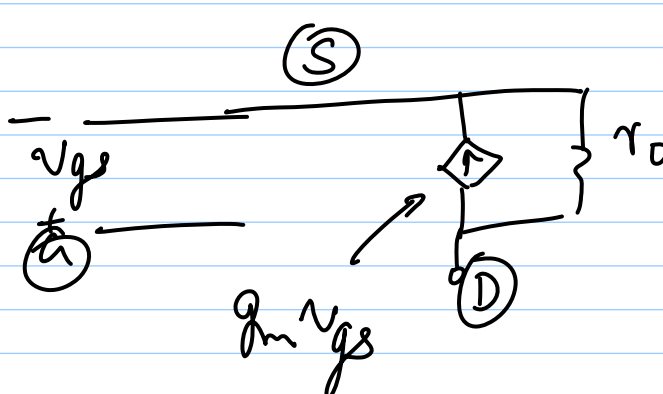
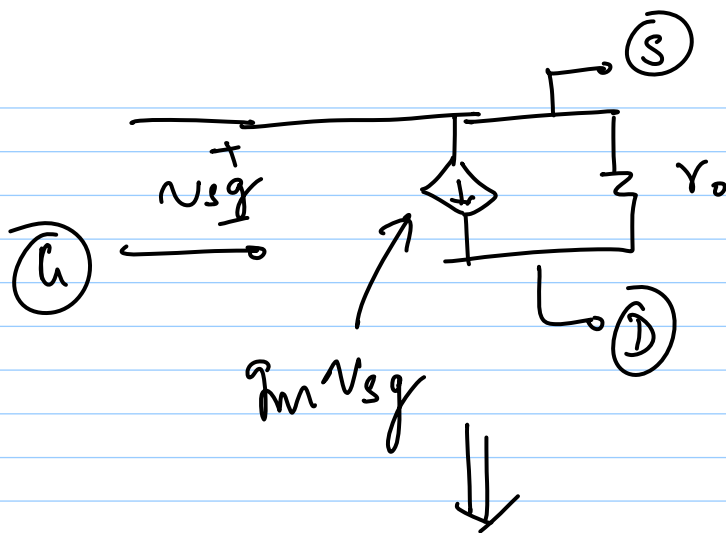


Small-signal eq.

$$y_{11} = 0, \quad y_{12} = 0$$

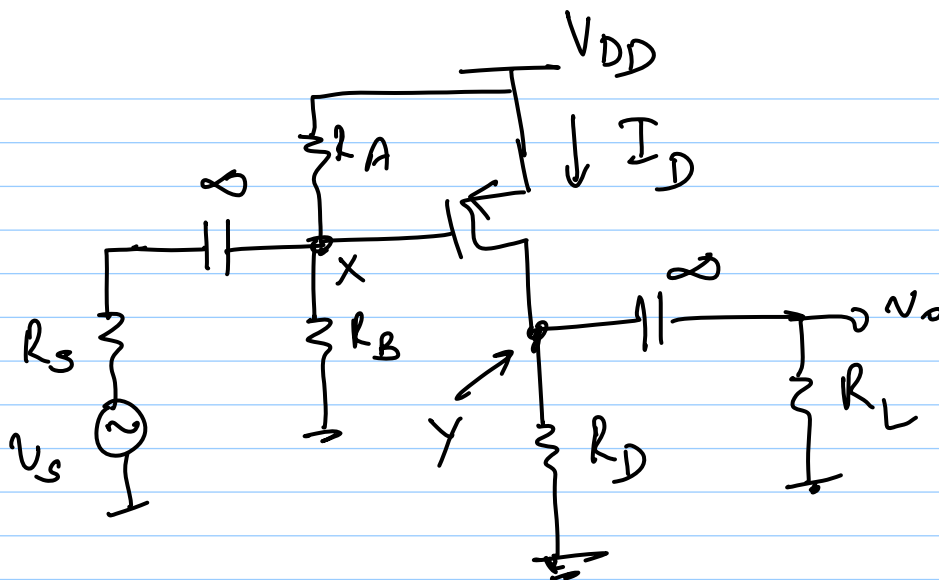
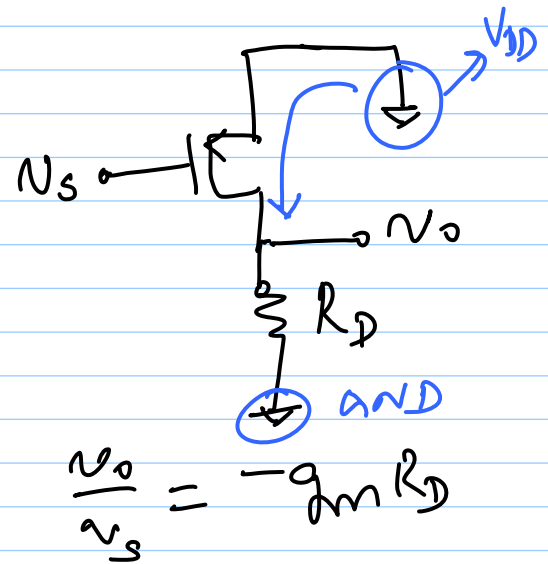
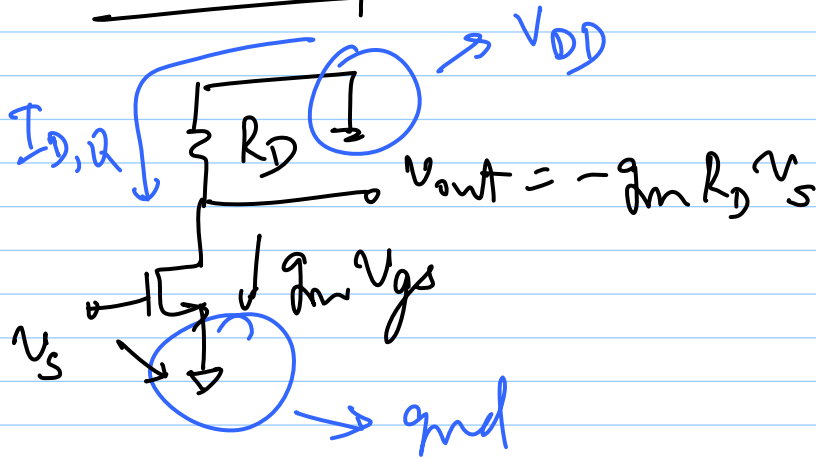
$$y_{21} = g_m = \mu_p C_{ox} \frac{W}{L} (V_{SA} - V_T)$$

$$y_{22} = \frac{1}{r_o} = \lambda I_D = g_o$$



same
as
NMOS
device

C.S. Amp



$$\# \quad v_x \approx v_s \Rightarrow R_A \parallel R_B \gg R_s$$

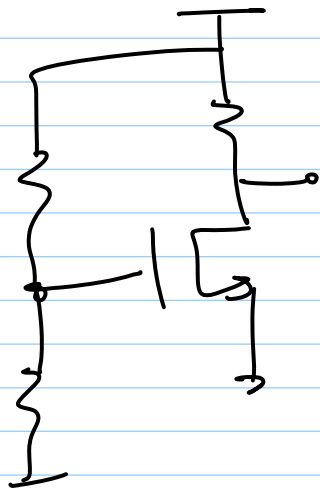
$$V_{Y,Q} = I_D \cdot R_D$$

$$V_{X,Q} = \frac{R_B}{R_A + R_B} \cdot V_{DD}$$

for sat.,

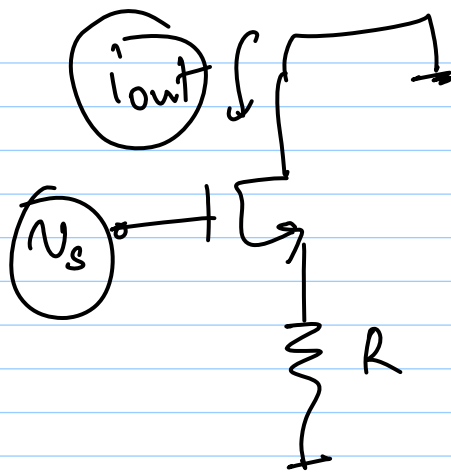
$$V_{Y,Q} \leq V_{X,Q} + V_{TP}$$

$$I_D \cdot R_D \leq () V_{DD} + V_{TP}$$



$$V_{O,Q} = V_{DD} - I_D R_D$$

$$V_{DD} - I_D R_D \gg V_{A,Q} - V_{T_n}$$



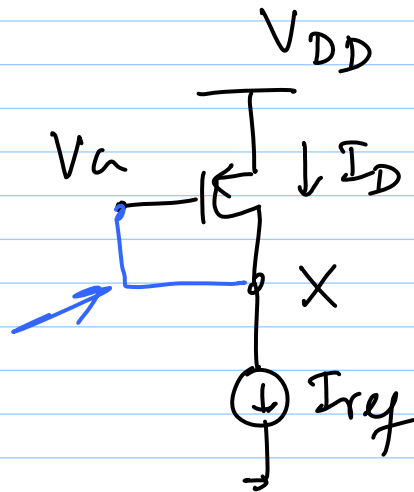
$$i_{out} = \frac{g_m}{1 + g_m R} \cdot v_{in}$$

$$g_m \gg 1/R$$

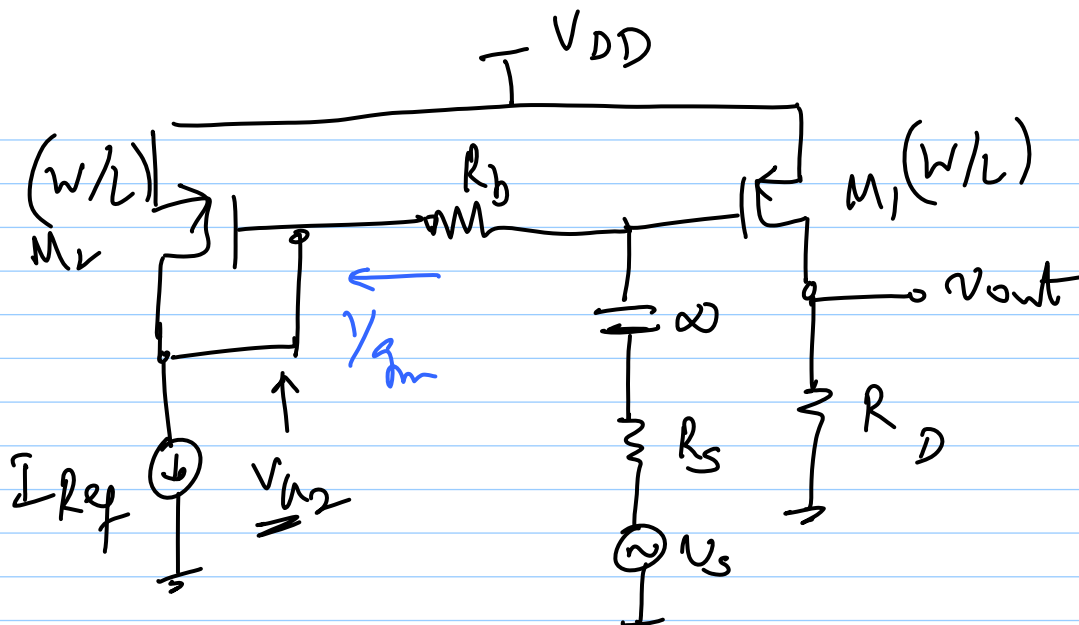
$$\Rightarrow i_{out} = \frac{v_{in}}{R}$$

Bias Stabilisation

(I)

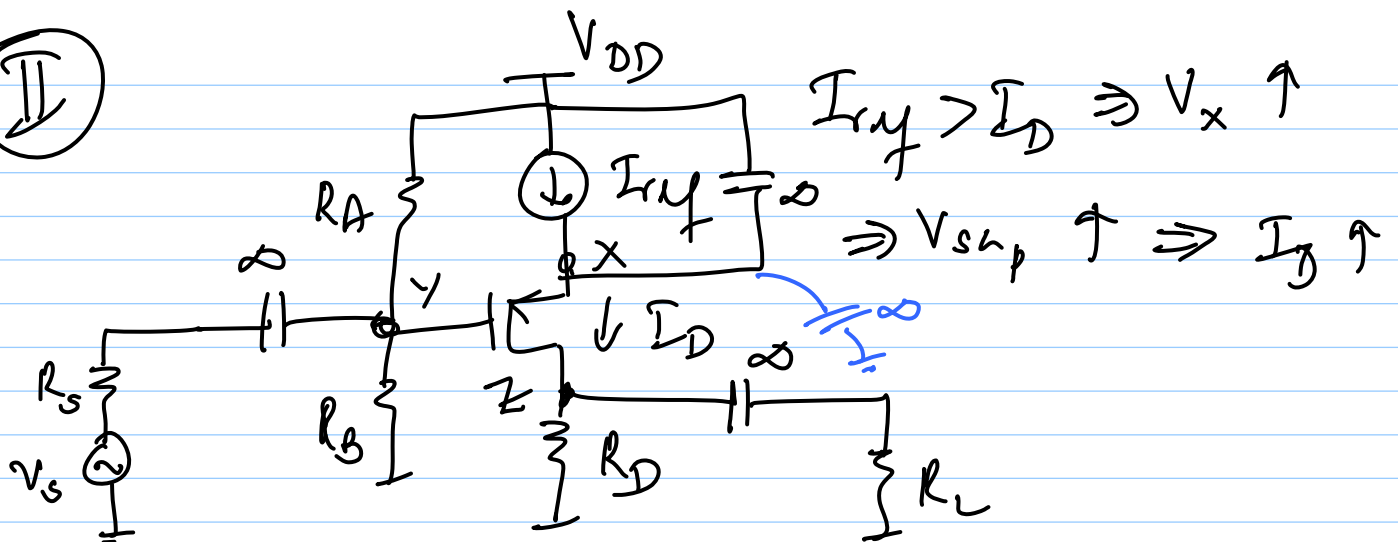


$I_D > I_{ref} \Rightarrow V_x \uparrow$
 $\Rightarrow$ need to $\uparrow V_a$



Current mirror

II



$$V_{z,Q} = I_{ref} \cdot R_D$$

$$V_{y,Q} = \frac{R_B}{R_A + R_B} \cdot V_{DD}$$

$$V_{x,Q} = V_{y,Q} + V_{sh}$$

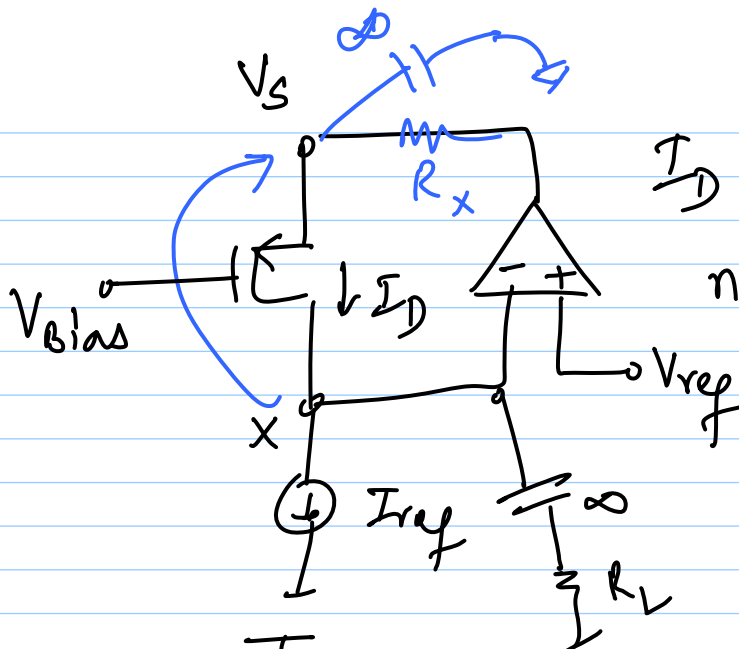
cutoff

$$I_{tot.} = I_D + i_d$$

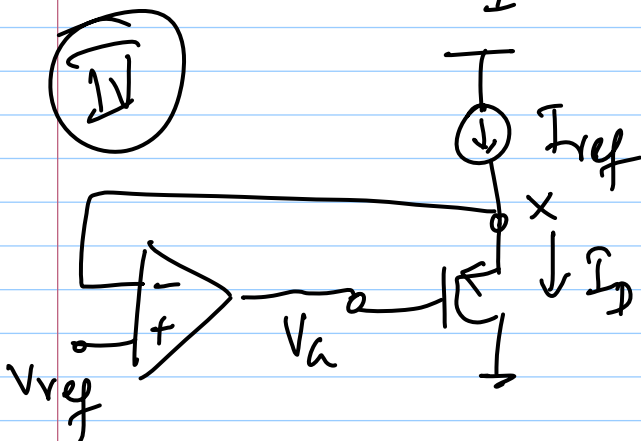
triode

$$V_D = V_a + V_T$$

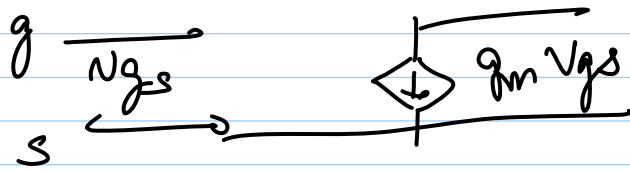
III



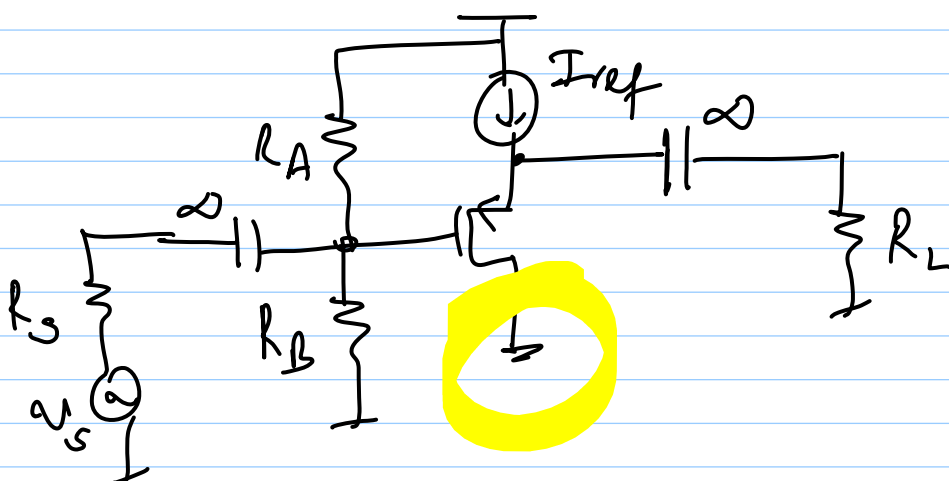
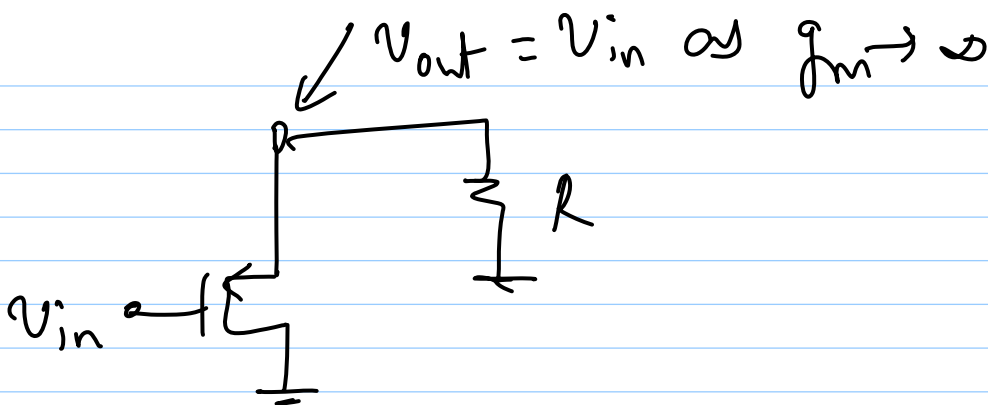
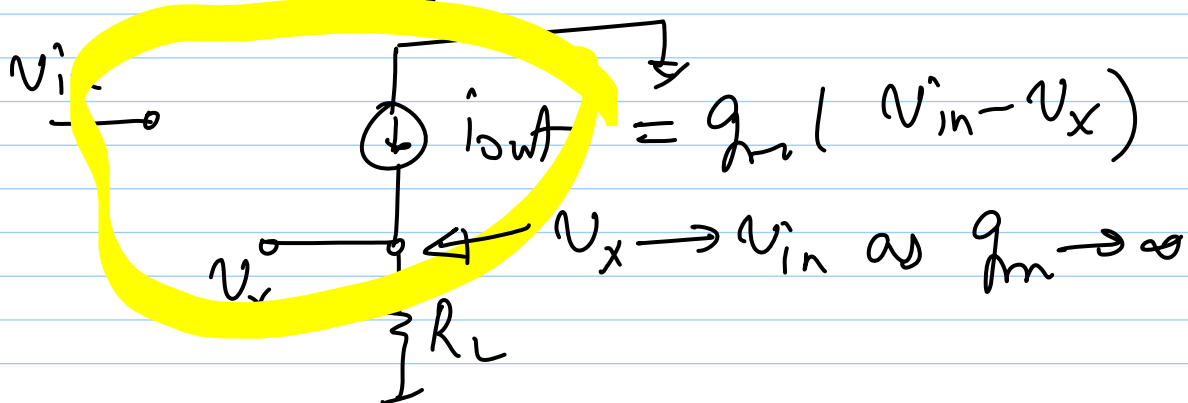
IV



Controlled Sources



① VCVS gain = 1



Common
Drain
Amp.
(PMOS)